RENESAS HD74LV1G00A

2-input NAND Gate

REJ03D0062-0800 Rev.8.00 Mar 21, 2008

Description

The HD74LV1G00A has two–input NAND gate in a 5 pin package. Low voltage and high-speed operation is suitable for the battery powered products (e.g., notebook computers), and the low power consumption extends the battery life.

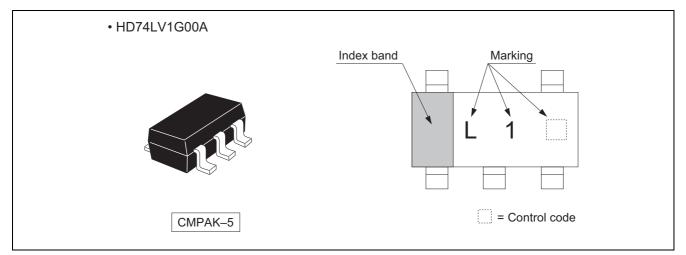
Features

- The basic gate function is lined up as Renesas uni logic series.
- Supplied on emboss taping for high-speed automatic mounting.
- Electrical characteristics equivalent to the HD74LV00A Supply voltage range : 1.65 to 5.5 V Operating temperature range : -40 to +85°C
- All inputs V_{IH} (Max.) = 5.5 V (@V_{CC} = 0 V to 5.5 V) All outputs V_O (Max.) = 5.5 V (@V_{CC} = 0 V)
- Output current $\pm 6 \text{ mA}$ (@V_{CC} = 3.0 V to 3.6 V), $\pm 12 \text{ mA}$ (@V_{CC} = 4.5 V to 5.5 V)
- All the logical input has hysteresis voltage for the slow transition.
- Ordering Information

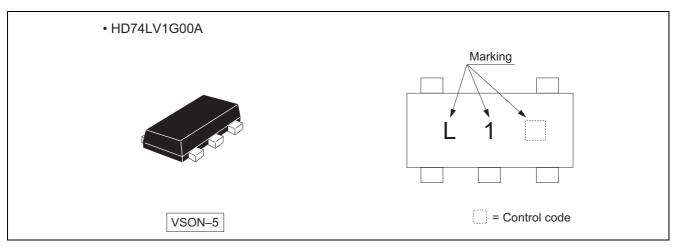
Part Name	Package Type	Package Code (Previous Code)	Package Abbreviation	Taping Abbreviation (Quantity)
HD74LV1G00ACME	CMPAK–5 pin	PTSP0005ZC-A (CMPAK-5V)	СМ	E (3000 pcs/reel)
HD74LV1G00AVSE	VSON–5 pin	PUSN0005KA-A (TNP-5DV)	VS	E (3000 pcs/reel)

Note: Please consult the sales office for the above package availability.

Outline and Article Indication



Outline and Article Indication



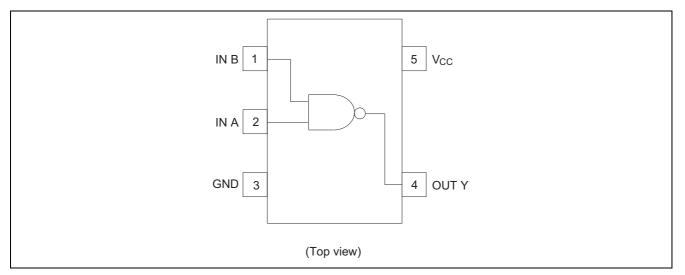
Function Table

Inp	Inputs						
A	В	Output Y					
L	L	Н					
L	Н	Н					
Н	L	Н					
Н	Н	L					

H : High level

L : Low level

Pin Arrangement



Absolute Maximum Ratings

ltem	Symbol	Ratings	Unit	Test Conditions
Supply voltage range	V _{cc}	-0.5 to 7.0	V	
Input voltage range ^{*1}	VI	-0.5 to 7.0	V	
Output voltage range *1, 2	Vo	–0.5 to V _{CC} + 0.5	V	Output : H or L
	٧O	-0.5 to 7.0	v	V _{CC} : OFF
Input clamp current	I _{IK}	-20	mA	V ₁ < 0
Output clamp current	Ι _{ΟΚ}	±50	mA	$V_0 < 0 \text{ or } V_0 > V_{CC}$
Continuous output current	lo	±25	mA	$V_{\rm O} = 0$ to $V_{\rm CC}$
Continuous current through V _{CC} or GND	I _{CC} or I _{GND}	±50	mA	
Maximum power dissipation at Ta = 25° C (in still air) ^{*3}	Ρ _Τ	200	mW	
Storage temperature	Tstg	-65 to 150	°C	

Notes: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore no two of which may be realized at the same time.

1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

- 2. This value is limited to 5.5 V maximum.
- 3. The maximum package power dissipation was calculated using a junction temperature of 150°C.

Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage range	V _{cc}	1.65	5.5	V	
Input voltage range	VI	0	5.5	V	
Output voltage range	Vo	0	V _{CC}	V	
		—	1		$V_{CC} = 1.65$ to 1.95 V
	L.	—	2		$V_{CC} = 2.3$ to 2.7 V
	I _{OL}	—	6		V_{CC} = 3.0 to 3.6 V
		—	12	- mA	$V_{CC} = 4.5 \text{ to } 5.5 \text{ V}$
Output current	Іон	—	-1		V _{CC} = 1.65 to 1.95 V
		—	-2		V_{CC} = 2.3 to 2.7 V
		—	-6		$V_{CC} = 3.0 \text{ to } 3.6 \text{ V}$
		—	-12]	$V_{CC} = 4.5 \text{ to } 5.5 \text{ V}$
		0	300		$V_{CC} = 1.65$ to 1.95 V
Input transition rise or fall rate	Δt / Δv	0	200		V_{CC} = 2.3 to 2.7 V
Input transition rise or fall rate	$\Delta t / \Delta V$	0	100	ns / V	V_{CC} = 3.0 to 3.6 V
		0	20		V_{CC} = 4.5 to 5.5 V
Operating free-air temperature	Ta	-40	85	°C	

Note: Unused or floating inputs must be held high or low.

Electrical Characteristic

• $Ta = -40 \text{ to } 85^{\circ}C$

Item	Symbol	V _{cc} (V) *	Min	Тур	Max	Unit	Test condition
		1.65 to 1.95	V _{CC} ×0.75	_	—		
	V	2.3 to 2.7	V _{CC} ×0.7	_	—		
	VIH	3.0 to 3.6	V _{CC} ×0.7		_		
Input voltage		4.5 to 5.5	V _{CC} ×0.7	_	—	V	
		1.65 to 1.95	_	_	V _{CC} ×0.25	v	
	VIL	2.3 to 2.7	_	_	V _{CC} ×0.3		
	VIL	3.0 to 3.6	_	_	V _{CC} ×0.3		
		4.5 to 5.5	_	_	V _{CC} ×0.3		
		1.8	—	0.25	—		
Hysteresis voltage	V _H	2.5	—	0.30	—	V	$V_T^+ - V_T^-$
	VН	3.3	—	0.35	—	v	$v_{T} - v_{T}$
		5.0	—	0.45	—		
		Min to Max	V _{CC} -0.1	_	—		I _{OH} = -50 μA
		1.65	1.4	_	—	_	$I_{OH} = -1 \text{ mA}$
	V _{OH}	2.3	2.0	_	—		$I_{OH} = -2 \text{ mA}$
		3.0	2.48	_	—		I _{OH} =6 mA
		4.5	3.8		_	V	I _{OH} = -12 mA
Output voltage		Min to Max	_	_	0.1	v	I _{OL} = 50 μA
		1.65	_	_	0.3		I _{OL} = 1 mA
	V _{OL}	2.3	_		0.4		$I_{OL} = 2 \text{ mA}$
		3.0	—	_	0.44		$I_{OL} = 6 \text{ mA}$
		4.5	—	_	0.55		I _{OL} = 12 mA
Input current	I _{IN}	0 to 5.5	—		±1	μΑ	$V_{IN} = 5.5 \text{ V or GND}$
Quiescent supply current	I _{CC}	5.5	—	—	10	μA	$V_{IN} = V_{CC} \text{ or } GND,$ $I_O = 0$
Output leakage current	I _{OFF}	0	—	_	5	μA	V_{IN} or $V_O = 0$ to 5.5 V
Input capacitance	CIN	3.3	—	2.5		pF	$V_{IN} = V_{CC}$ or GND

Note: For conditions shown as Min or Max, use the appropriate values under recommended operating conditions.

Switching Characteristics

•	$V_{CC} =$	$1.8 \pm$	0.15	V
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ltem	Symbol	-	Га = 25°С		Ta = –40	to 85°C	Unit	Test	FROM	то
item	Symbol	Min	Тур	Max	Min	Max	Onit	Conditions	(Input)	(Output)
Propagation	t _{PLH}	—	12.7	23.1	1.0	25.5		C∟ = 15 pF	A or B	v
delay time	t _{PHL}		18.7	33.4	1.0	37.0	ns	$C_L = 50 \text{ pF}$	AUD	T

• $V_{CC} = 2.5 \pm 0.2 V$

Item	Symbol	٦	Ta = 25°C)	Ta = -40) to 85°C	Unit	Test	FROM	то
nem	Symbol	Min	Тур	Max	Min	Max	Unit	Conditions	(Input)	(Output)
Propagation	t _{PLH}	Ι	7.1	12.9	1.0	15.0	ns	C _L = 15 pF	A or B	v
delay time	t _{PHL}	_	9.6	16.6	1.0	20.0	115	$C_L = 50 \text{ pF}$	AUB	I

• $V_{CC} = 3.3 \pm 0.3 V$

ltem	Symbol	٦	Ta = 25°C	;	Ta = -40	to 85°C	Unit	Test	FROM	то
nem	Symbol	Min	Тур	Max	Min	Max	Unit	Conditions	(Input)	(Output)
Propagation	t _{PLH}	Ι	5.0	7.9	1.0	9.5	ns	C _L = 15 pF	A or B	v
delay time	t _{PHL}	_	6.9	11.4	1.0	13.0	-	$C_L = 50 \text{ pF}$	AUD	I

• VCC = 5.0 ± 0.5 V

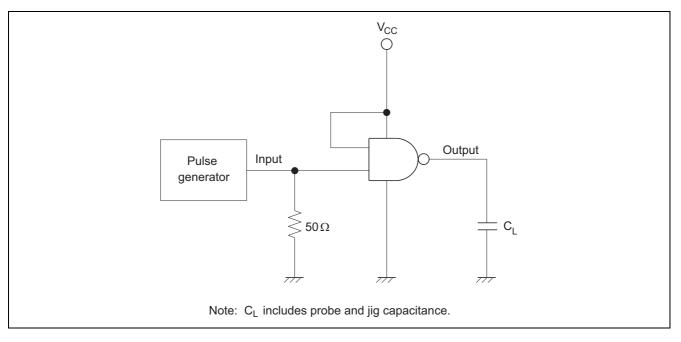
Item	Symbol	٦	Ta = 25°C	;	Ta = –40	to 85°C	Unit	Test	FROM	то
item	Symbol	Min	Тур	Max	Min	Max	Unit	Conditions	(Input)	(Output)
Propagation	t _{PLH}	Ι	3.6	5.5	1.0	6.5	ns	$C_{L} = 15 pF$	A or B	v
delay time	t _{PHL}	_	4.9	7.5	1.0	8.5	115	$C_L = 50 \text{ pF}$	AUD	I

Operating Characteristics

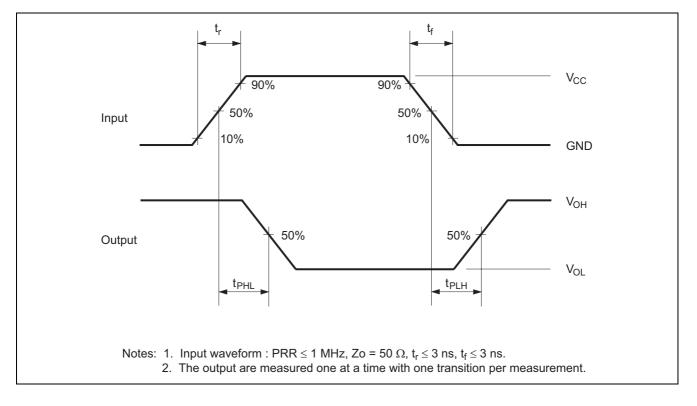
• $C_L = 50 \text{ pF}$

ltem	Symbol	V _{cc} (V)		Ta = 25°C		Unit	Test Conditions	
nem	Symbol		Min	Тур	Max	Onit	Test conditions	
Power dissipation	C _{PD}	3.3	_	9.5	-	ρF	f = 10 MHz	
capacitance	CPD	5.0	—	11.0		μr		

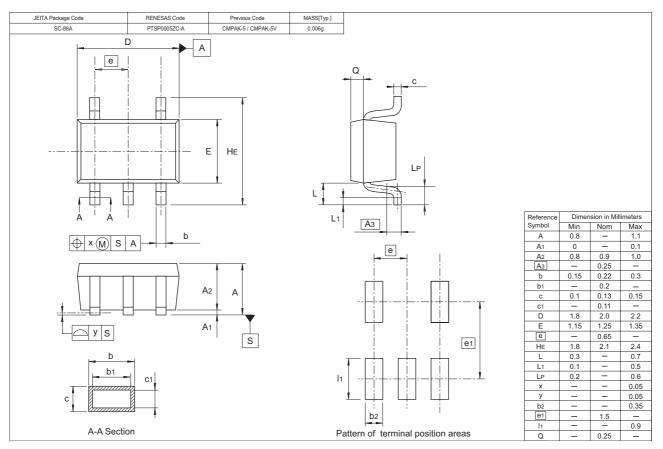
Test Circuit

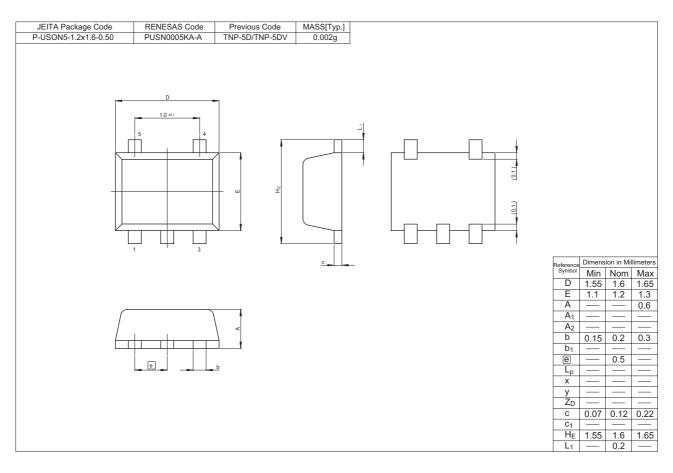


Waveforms



Package Dimensions





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